



STP40NS15

N-CHANNEL 150V - 0.042Ω - 40A TO-220

MESH OVERLAY™ MOSFET

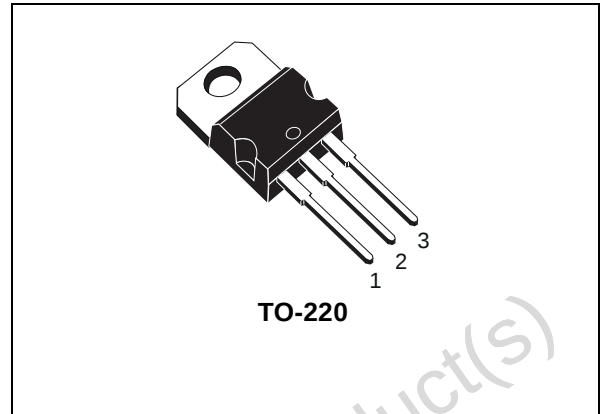
PRELIMINARY DATA

TYPE	V _{DSS}	R _{DS(on)}	I _D
STP40NS15	150 V	<0.052Ω	40A

- TYPICAL R_{DS(on)} = 0.042Ω
- EXTREMELY HIGH dv/dt CAPABILITY
- VERY LOW INTRINSIC CAPACITANCES
- GATE CHARGE MINIMIZED

DESCRIPTION

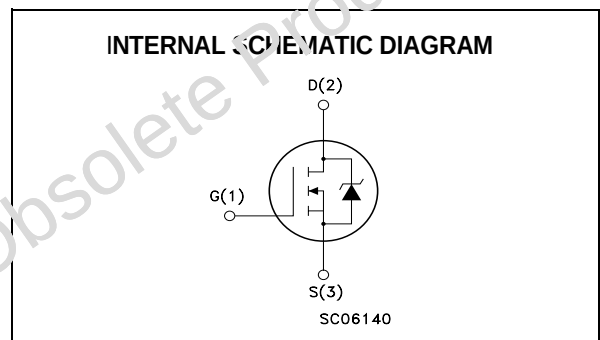
This powermos MOSFET is designed using the company's consolidated strip layout-based MESH OVERLAY™ process. This technology matches and improves the performances compared with standard parts from various sources.



TO-220

APPLICATIONS

- HIGH CURRENT SWITCHING
- UNINTERRUPTIBLE POWER SUPPLY (UPS)
- PRIMARY SWITCH IN ISOLATED DC-DC CONVERTERS



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{DS}	Drain-source Voltage (V _{GS} = 0)	150	V
V _{DGR}	Drain-gate Voltage (R _{GS} = 20 kΩ)	150	V
V _{GS}	Gate-source Voltage	±20	V
I _D	Drain Current (continuous) at T _C = 25°C	40	A
I _C	Drain Current (continuous) at T _C = 100°C	25	A
I _{DM} (•)	Drain Current (pulsed)	160	A
P _{TOT}	Total Dissipation at T _C = 25°C	140	W
	Derating Factor	0.933	W/°C
dv/dt	Peak Diode Recovery voltage slope	9	V/ns
T _{stg}	Storage Temperature	-65 to 175	°C
T _j	Max. Operating Junction Temperature	175	°C

(•)Pulse width limited by safe operating area

STP40NS15

THERMAL DATA

Rthj-case	Thermal Resistance Junction-case Max	1.07	°C/W
Rthj-amb	Thermal Resistance Junction-ambient Max	62.5	°C/W
Rthc-sink	Thermal Resistance Case-sink Typ	0.5	°C/W
T _I	Maximum Lead Temperature For Soldering Purpose	300	°C

AVALANCHE CHARACTERISTICS

Symbol	Parameter	Max Value	Unit
I _{AR}	Avalanche Current, Repetitive or Not-Repetitive (pulse width limited by T _j max)	40	A
E _{AS}	Single Pulse Avalanche Energy (starting T _j = 25 °C, I _D = I _{AR} , V _{DD} = 50 V)	500	mJ

ELECTRICAL CHARACTERISTICS (T_{case} = 25 °C UNLESS OTHERWISE SPECIFIED)

OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V _{(BR)DSS}	Drain-source Breakdown Voltage	I _D = 250 µA, V _{GS} = 0	150			V
I _{DSS}	Zero Gate Voltage Drain Current (V _{GS} = 0)	V _{DS} = Max Rating V _{DS} = Max Rating, T _C = 125 °C			1 10	µA µA
I _{GSS}	Gate-body Leakage Current (V _{DS} = 0)	V _{GS} = ±20V			±100	nA

ON (1)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = 250µA	2	3	4	V
R _{DS(on)}	Static Drain-source On Resistance	V _{GS} = 10V, I _D = 40 A		0.044	0.052	Ω
I _{D(on)}	On State Drain Current	V _{DS} > I _{D(on)} × R _{DS(on)max} , V _{GS} = 10V	40			A

DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g _{fs} (1)	Forward Transconductance	V _{DS} > I _{D(on)} × R _{DS(on)max} , I _D = 20A		20		S
C _{iss}	Input Capacitance	V _{DS} = 25V, f = 1 MHz, V _{GS} = 0		2400		pF
C _{oss}	Output Capacitance			380		pF
C _{rss}	Reverse Transfer Capacitance			160		pF

ELECTRICAL CHARACTERISTICS (CONTINUED)

SWITCHING ON

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on Delay Time	$V_{DD} = 75V, I_D = 20A$ $R_G = 4.7\Omega, V_{GS} = 10V$ (see test circuit, Figure 3)		25		ns
t_r	Rise Time			45		ns
Q_g	Total Gate Charge	$V_{DD} = 120V, I_D = 40A,$ $V_{GS} = 10V$		100	110	nC
Q_{gs}	Gate-Source Charge			17		nC
Q_{gd}	Gate-Drain Charge			47		nC

SWITCHING OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(off)}$	Turn-off Delay Time	$V_{DD} = 75V, I_D = 20A$ $R_G = 4.7\Omega, V_{GS} = 10V$ (see test circuit, Figure 3)		85		ns
T_f	Fall Time					
$t_{r(Voff)}$	Off-voltage Rise Time	$V_{clamp} = 120V, I_D = 20A,$ $R_G = 4.7\Omega, V_{GS} = 10V$ (see test circuit, Figure 5)		47		ns
t_f	Fall Time			35		ns
t_c	Cross-over Time			70		ns

SOURCE DRAIN DIODE

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain Current				40	A
$I_{SDM(2)}$	Source-drain Current (pulsed)				160	A
$V_{SD(1)}$	Forward On Voltage	$I_{SD} = 40A, V_{GS} = 0$			1.5	V
t_{rr}	Reverse Recovery Time	$I_{SD} = 40A, di/dt = 100A/\mu s,$ $V_{DD} = 50V, T_j = 150^\circ C$ (see test circuit, Figure 5)		270		ns
Q_{rr}	Reverse Recovery Charge			200		nC
I_{RRM}	Reverse Recovery Current			1.5		A

Note: 1. Pulsed: Pulse duration = 300 μs , duty cycle 1.5 %.
2. Pulse width limited by safe operating area.

Fig. 1: Unclamped Inductive Load Test Circuit

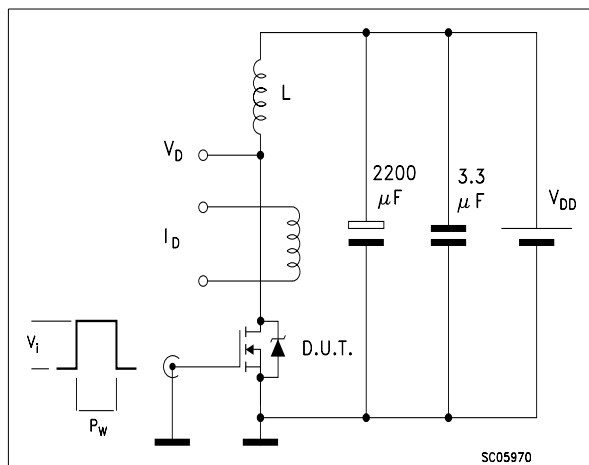


Fig. 2: Unclamped Inductive Waveform

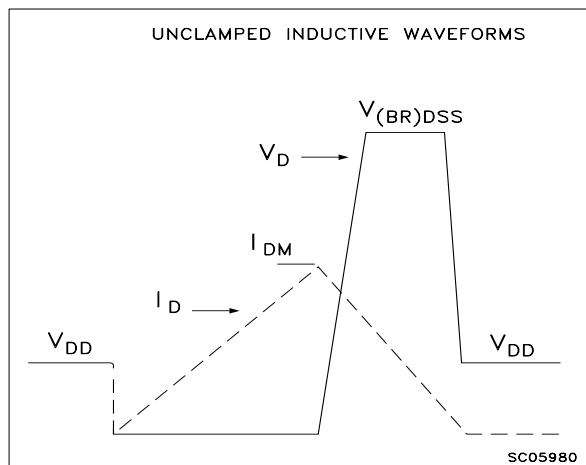


Fig. 3: Switching Times Test Circuit For Resistive Load

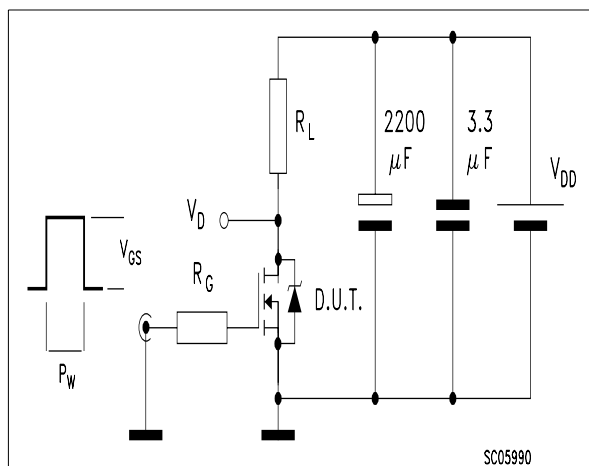


Fig. 4: Gate Charge test Circuit

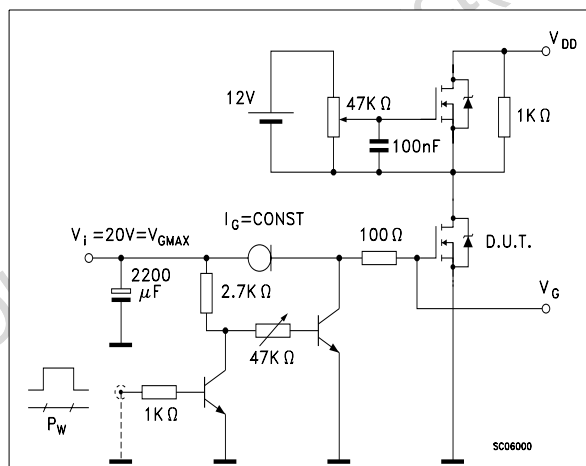
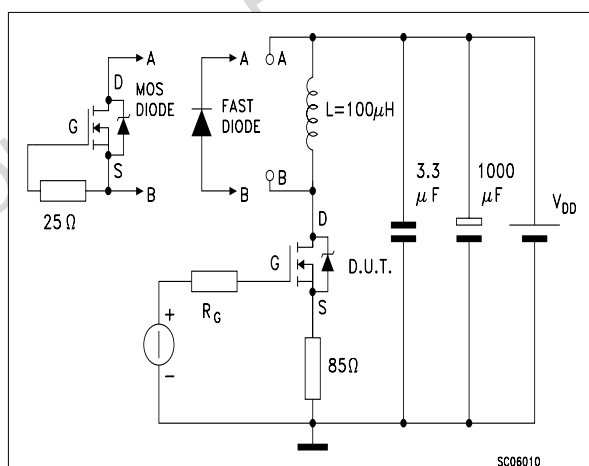
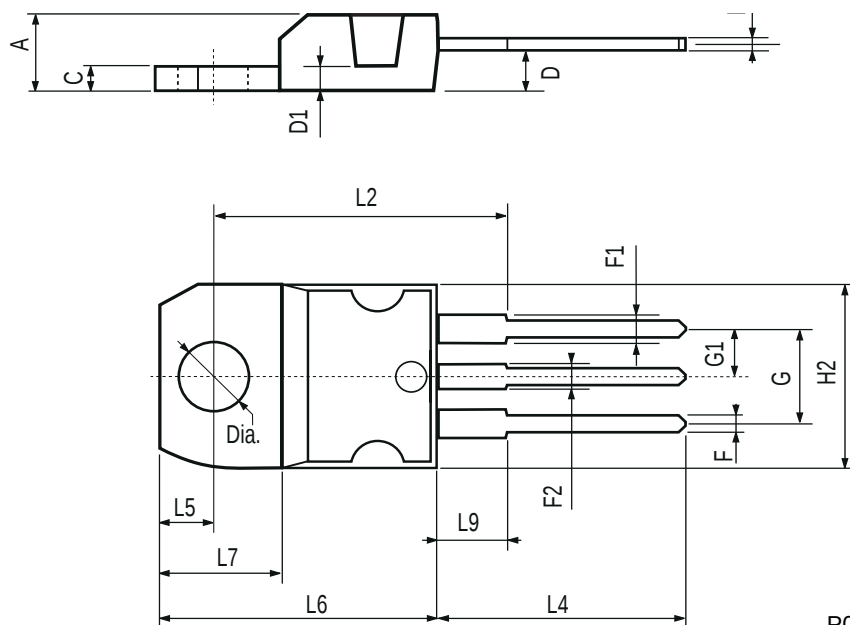


Fig. 5: Test Circuit For Inductive Load Switching And Diode Recovery Times



TO-220 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.40		4.60	0.173		0.181
C	1.23		1.32	0.048		0.051
D	2.40		2.72	0.094		0.107
D1		1.27			0.050	
E	0.49		0.70	0.019		0.027
F	0.61		0.88	0.024		0.034
F1	1.14		1.70	0.044		0.067
F2	1.14		1.70	0.044		0.067
G	4.95		5.15	0.194		0.203
G1	2.4		2.7	0.094		0.106
H2	10.0		10.40	0.393		0.409
L2		16.4			0.645	
L4	13.0		14.0	0.511		0.551
L5	2.65		2.95	0.104		0.116
L6	15.25		15.75	0.600		0.620
L7	6.2		6.6	0.244		0.260
L9	3.5		3.93	0.137		0.154
DIA.	3.75		3.85	0.147		0.151



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